TPD-8D12

GaAs PIN photodiode chip

FEATURES:

- Optimized for fiber optic application.
- Low dark current and low capacitance.

ELECTRO-OPTICAL CHARACTERISTICS:

PARAMETERS	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Responsivity	R	0.55	0.6	0.63	A/W	V_R=5V, λ=850nm
Forward Current	I_F	100			μA	V_F=1V
Dark Current	I_D		0.2	1	nA	V_R=5V
Breakdown Voltage	V_{BD}	50	85		V	I_R=10μA
Capacitance	C		0.7	1.0	pF	V_R=5V, f=1 MHz

Fig. 1 Typical Dark Current and Forward Current

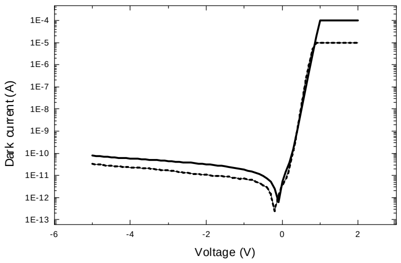


Fig. 2 Typical Photo-Current

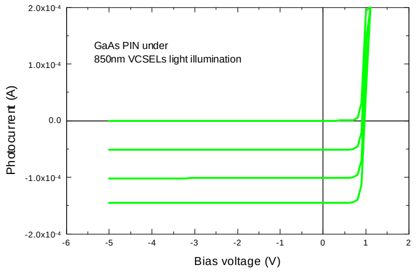


Fig. 3 Typical Breakdown Curve

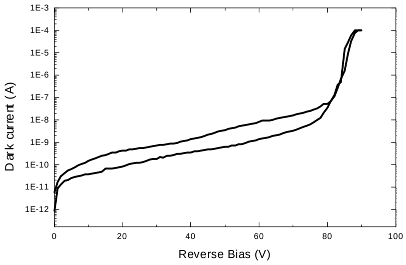
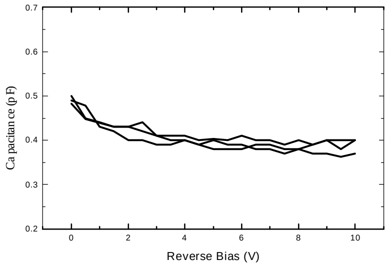


Fig. 4 Typical C-V Curve



OUTLINE DIAGRAM:

- Chip size is typical 250x250 μm square.
- Sensitive area is typical 100 μm in diameter.